

**SOT-23**


- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

**MARKING: G1**
**Features**

- Complementary to MMBT5401
- Epitaxial planar die construction
- Power Dissipation of 300mW

**Maximum Ratings**

(Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter -Base Voltage	V <sub>EBO</sub>	6	V
Collector Current-Continuous	I <sub>c</sub>	600	mA
Collector Power Dissipation	P <sub>c</sub>	300	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55-+150	°C
Thermal resistance From junction to ambient	R <sub>θJA</sub>	416	°C/W

**Electrical Characteristics**

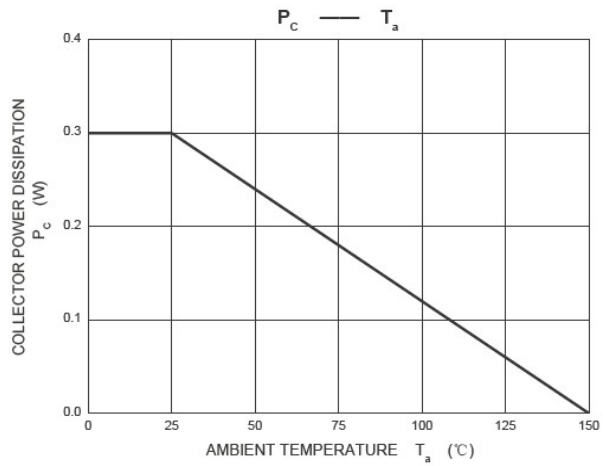
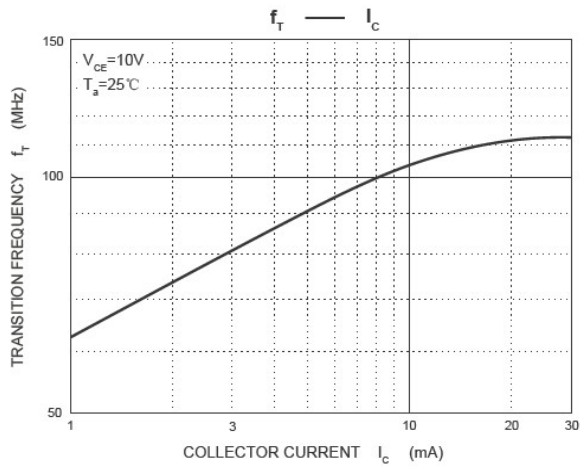
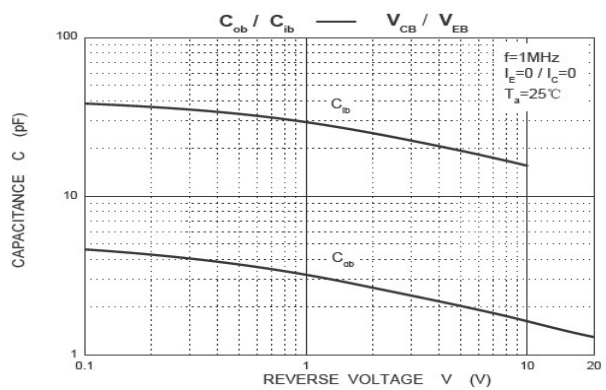
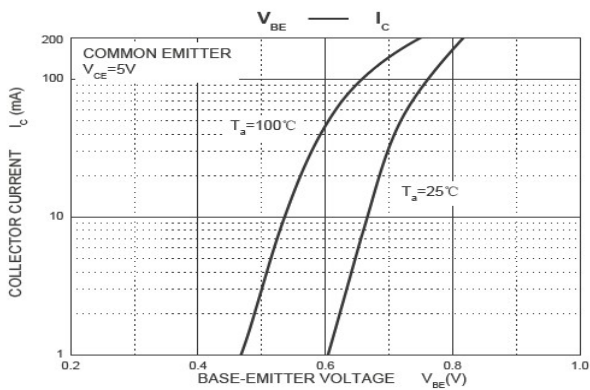
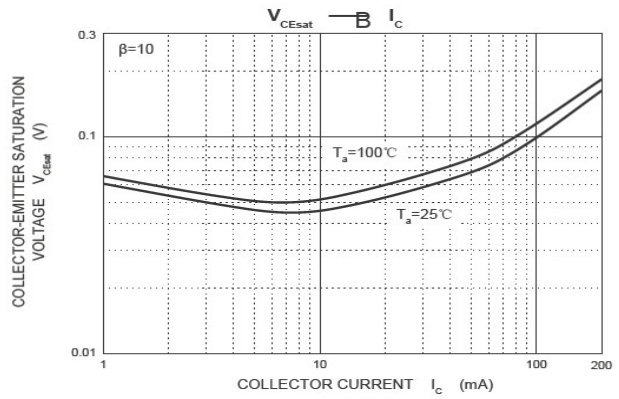
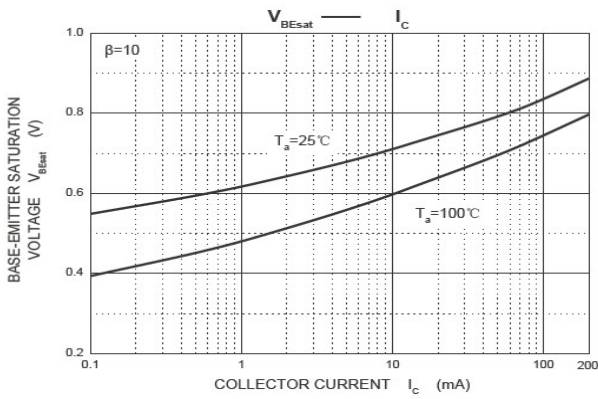
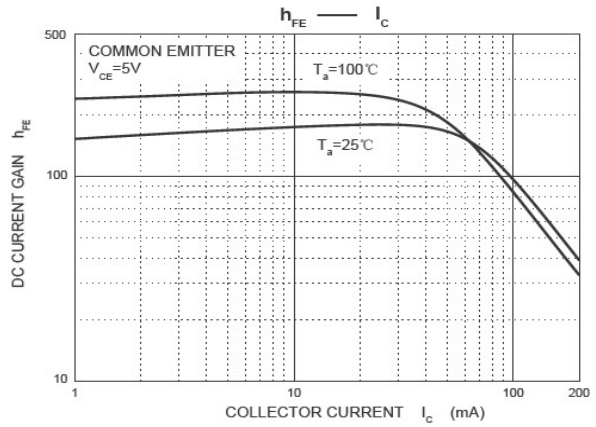
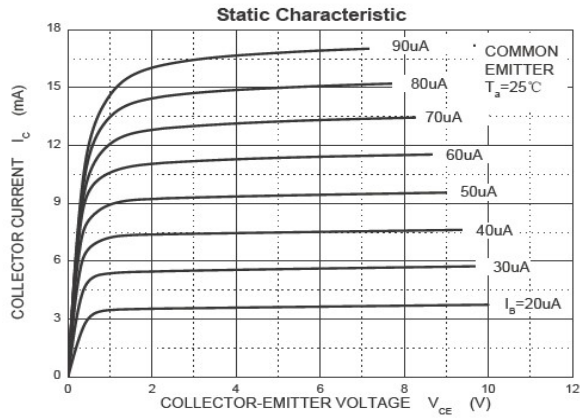
(Ratings at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbols	Test Condition	Limits		Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	I <sub>C</sub> =100μA, I <sub>E</sub> =0	180		V
Collector-emitter breakdown voltage	V(BR)CEO *	I <sub>C</sub> =1mA, I <sub>B</sub> =0	160		V
Emitter-base breakdown voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =120V, I <sub>E</sub> =0		50	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0		50	nA
DC current gain	hFE(1) *	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	80		
	hFE(2) *	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	100	300	
	hFE(3) *	V <sub>CE</sub> =5V, I <sub>C</sub> =50mA	30		
Collector-emitter saturation voltage	VCE(sat)1 *	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.15	V
	VCE(sat)2 *	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA		0.20	V
Base -emitter saturation voltage	VBE(sat)1 *	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		1.00	V
	VBE(sat)2 *	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA		1.00	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA, f=100MHz	100	300	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		6	pF

\*Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2.0%

**CLASSIFICATION OF hFE(2)**

HFE	100-300	
RANK	L	H
RANGE	100-200	200-300



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